

ABSTRACT

Disclosed is a wafer marking method using a laser for marking a wafer having processing tape attached thereto. The disclosed laser marking method comprises the steps of: penetrating a 532-nm wavelength laser beam through the processing tape attached to one side of the wafer; and performing marking on the one side of the wafer by moving the 532-nm wavelength laser beam at a predetermined velocity, wherein the 532-nm wavelength laser beam has a frequency of 8 kHz to 40 kHz, and an output power of 0.8 W to 2 W.